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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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## TECHNICAL DATA

## NPN POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/525

Devices Qualified Level

2N6546 2N6547

JAN JANTX JANTXV

#### **MAXIMUM RATINGS**

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Ratings	Symbol	2N6546	2N6547	Units
Collector-Emitter Voltage	$V_{CEO}$	300	400	Vdc
Collector-Base Voltage	V <sub>CEX</sub>	600	850	Vdc
Emitter-Base Voltage	$V_{EBO}$	8		Vdc
Base Current	$I_{B}$	10		Adc
Collector Current	$I_{C}$	15		Adc
Total Power Dissipation @ $T_C = +25^{\circ}C^{(1)}$	D	175 100		W
@ $T_C = +100^0 C^{(1)}$	$P_{T}$			W
Operating & Storage Temperature Range	Top, Tstg	-65 to +200		°C

## THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.0	<sup>0</sup> C/W

<sup>1)</sup> Between  $T_C = +25^{\circ}C$  and  $T_C = +200^{\circ}C$ , linear derating factor (average) = 1.0 W/ $^{\circ}C$ 



\*See Appendix A for Package Outline

#### **ELECTRICAL CHARACTERISTICS**

Characteristi	cs	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					_
Collector-Emitter Breakdown Voltage					
$I_C = 100 \text{ mAdc}$	2N6546	$V_{(BR)CEO}$	300		Vdc
	2N6547		400		
Collector-Emitter Cutoff Current					
$V_{CE} = 600 \text{ Vdc}; V_{BE} = 1.5 \text{ Vdc}$	2N6546	$I_{CEX}$		1.0	mAdc
$V_{CE} = 850 \text{ Vdc}; V_{BE} = 1.5 \text{ Vdc}$	2N6547			1.0	
Emitter-Base Cutoff Current		т			mAdc
$V_{EB} = 8 \text{ Vdc}$		$I_{\mathrm{EBO}}$		1.0	mAdc

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#### 2N6546, 2N6547 JAN SERIES

### **ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS (3)	•			
Forward-Current Transfer Ratio				
$I_C = 1 \text{ Adc}; \ V_{CE} = 2 \text{ Vdc}$	,	15		
$I_C = 5 \text{ Adc}; \ V_{CE} = 2 \text{ Vdc}$	$h_{ m FE}$	12	60	
$I_C = 10 \text{ Adc}; \ V_{CE} = 2 \text{ Vdc}$		6		
Base-Emitter Saturated Voltage	V			Vdc
$I_B = 2.0 \text{ Adc}; I_C = 10 \text{ Adc}$	V <sub>BE(sat)</sub>		1.6	
Collector-Emitter Saturated Voltage				
$I_B = 2.0 \text{ Adc}; I_C = 10 \text{ Adc}$	V <sub>CE(sat)</sub>		1.5	Vdc
$I_B = 3.0 \text{ Adc}; I_C = 15 \text{ Adc}$			5.0	
DYNAMIC CHARACTERISTICS				
Magnitude of Common-Emitter Small-Signal Short-Circuit				
Forward Current Transfer Ratio	h <sub>fe</sub>			
$I_C = 0.5 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1 \text{ MHz}$		6.0	30	
Output Capacitance	C			nE
$V_{CB} = 10 \text{ Vdc}, I_E = 0, 0.1 \text{ MHz} \le f \le 1.0 \text{ MHz}$	$C_{obo}$		500	pF
SWITCHING CHARACTERISTICS				
Turn-On Time	t on		1.0	Ша
$V_{CC} = 250 \text{ Vdc}$ ; $I_C = 10 \text{ Adc}$ ; $I_{B1} = I_{B2} = 2 \text{ Adc}$	On		1.0	μs
Turn-Off Time	<sup>t</sup> off		4.7	Ше
$V_{CC} = 250 \text{ Vdc}; I_C = 10 \text{ Adc}; I_{B1} = I_{B2} = 2 \text{ Adc}$	OH		4.7	μs

#### SAFE OPERATING AREA

### DC Tests

 $T_C = +25^{\circ}C$ ;  $t_p = 1$  s; 1 cycle (See Figure 3 of MIL-PRF-19500/525)

#### Test 1

 $V_{CE} = 11.7 \text{ Vdc}$ ;  $I_C = 15 \text{ Adc}$ 

#### Test 2

 $V_{CE} = 20 \text{ Vdc}; I_{C} = 8.75 \text{ Adc}$ 

#### Test 3

 $V_{CE} = 250 \text{ Vdc}; I_C = 45 \text{ mAdc}$  2N6546  $V_{CE} = 350 \text{ Vdc}; I_C = 30 \text{ mAdc}$  2N6547

#### **Unclamped Inductive IOAD**

 $T_C = +25^{\circ}C$ ; duty cycle  $\leq 10\%$ ;  $R_S = 0.1 \Omega$ ;  $t_r = t_f \leq 500 \eta s$  (See Figure 4 of MIL-PRF-19500/525)

#### Test 1

Tp = 5 ms; (vary to obtain  $I_C$ );  $R_{BB1}$  = 15  $\Omega$ ;  $V_{BB}1$  = 38.5 Vdc;  $R_{BB2}$  = 50  $\Omega$ ;

 $V_{BB2}$  = -4 Vdc;  $V_{CC}$  = 20 Vdc; IC = 15 Adc; L = 10  $\mu H$ 

#### Test 2

Tp = 5 ms; (vary to obtain  $I_C$ );  $R_{BB1} = 15 \Omega$ ;  $V_{BB}1 = 38.5 \text{ Vdc}$ ;  $R_{BB2} = 50 \Omega$ ;

 $V_{BB2} = -4 \text{ Vdc}; V_{CC} = 20 \text{ Vdc}; IC = 100 \text{ mAdc}; L = 1 \text{ mH}$ 

## **Clamped Inductive Load**

 $T_A = +25^{\circ}C$ ; duty cycle  $\leq 5\%$ ; Tp = 1.5 ms; (vary to obtain  $I_C$ );  $V_{CC} = 20$  Vdc;  $I_C = 8$  Adc;  $L = 180 \mu H$ 

(See Figure 5 of MIL-PRF-19500/525)

Clamped Voltage = 350 Vdc 2N6546 Clamped Voltage = 450 Vdc 2N6547

3.) Pulse Test: Pulse Width =  $300\mu s$ , Duty Cycle  $\leq 2.0\%$ .